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LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

Applicant:	Bo Su	Chen	et	al.

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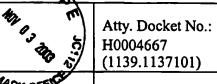
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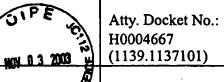
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Atty. Docket No.: H0004667 (1139.1137101)

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	$M \cdot 1 \cdot 1 \cdot 00 \cdot 00 \cdot 00 \cdot 00 \cdot 00 \cdot 00 $

EXAMINER: | Liebelle K. (MM Ille CONSIDERED: 2/22/06 EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.